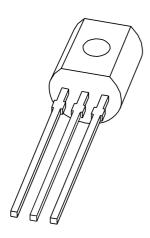
DISCRETE SEMICONDUCTORS

DATA SHEET



2N4126PNP general purpose transistor

Product specification Supersedes data of September 1994 File under Discrete Semiconductors, SC04 1997 Mar 25





PNP general purpose transistor

2N4126

FEATURES

- Low current (max. 200 mA)
- Low voltage (max. 25 V).

APPLICATIONS

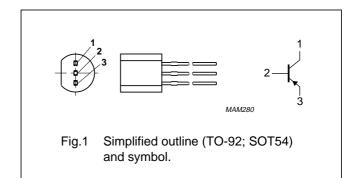
• General purpose switching and amplification, e.g. small-signal audio-frequency applications.

DESCRIPTION

PNP transistor in a TO-92; SOT54 plastic package. NPN complement: 2N4124.

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | collector |
| 2 | base |
| 3 | emitter |



QUICK REFERENCE DATA

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------------|---------------------------|---|------|------|------|
| V_{CBO} | collector-base voltage | open emitter | _ | -25 | ٧ |
| V_{CEO} | collector-emitter voltage | open base | _ | -25 | V |
| I _{CM} | peak collector current | | _ | -300 | mA |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | _ | 500 | mW |
| h _{FE} | DC current gain | $I_C = -2 \text{ mA}; V_{CE} = -1 \text{ V}$ | 120 | 360 | |
| f _T | transition frequency | $I_C = -10 \text{ mA}; V_{CE} = -20 \text{ V}; f = 100 \text{ MHz}$ | 250 | _ | MHz |

PNP general purpose transistor

2N4126

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------------|-------------------------------|----------------------------------|------|------|------|
| V _{CBO} | collector-base voltage | open emitter | _ | -25 | V |
| V_{CEO} | collector-emitter voltage | open base | _ | -25 | V |
| V _{EBO} | emitter-base voltage | open collector | _ | -4 | V |
| I _C | collector current (DC) | | _ | -200 | mA |
| I _{CM} | peak collector current | | _ | -300 | mA |
| I _{BM} | peak base current | | _ | -100 | mA |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C; note 1 | _ | 500 | mW |
| T _{stg} | storage temperature | | -65 | +150 | °C |
| Tj | junction temperature | | _ | 150 | °C |
| T _{amb} | operating ambient temperature | | -65 | +150 | °C |

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|---------------------|---|------------|-------|------|
| R _{th j-a} | thermal resistance from junction to ambient | note 1 | 250 | K/W |

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|--------------------|--------------------------------------|---|------|------|------|
| I _{CBO} | collector cut-off current | I _E = 0; V _{CB} = -20 V | _ | -50 | nA |
| I _{EBO} | emitter cut-off current | $I_C = 0; V_{EB} = -3 \text{ V}$ | _ | -50 | nA |
| h _{FE} | DC current gain | $I_C = -2 \text{ mA}; V_{CE} = -1 \text{ V}; \text{ note 1}$ | 120 | 360 | |
| | | I _C = -50 mA; V _{CE} = -1 V; note 1 | 60 | _ | |
| V _{CEsat} | collector-emitter saturation voltage | $I_C = -50 \text{ mA}$; $I_B = -5 \text{ mA}$; note 1 | _ | -400 | mV |
| V _{BEsat} | base-emitter saturation voltage | $I_C = -50 \text{ mA}$; $I_B = -5 \text{ mA}$; note 1 | _ | -950 | mV |
| C _c | collector capacitance | $I_E = i_e = 0$; $V_{CB} = -5$ V; $f = 1$ MHz | _ | 4.5 | pF |
| C _e | emitter capacitance | $I_C = I_c = 0$; $V_{EB} = -0.5 \text{ V}$; $f = 1 \text{ MHz}$ | _ | 10 | pF |
| f _T | transition frequency | $I_C = -10 \text{ mA}; V_{CE} = -20 \text{ V}; f = 100 \text{ MHz}$ | 250 | _ | MHz |
| F | noise figure | $I_C = -100 \mu A$; $V_{CE} = -5 V$; $R_S = 1 kΩ$; $f = 10 Hz$ to 15.7 kHz | _ | 4 | dB |

Note

1. Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02$.

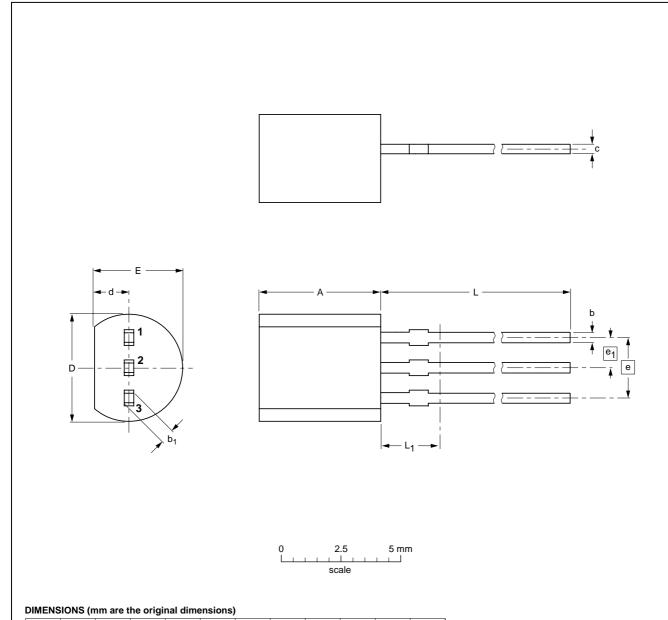
PNP general purpose transistor

2N4126

PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



| UNIT | A | b | b ₁ | С | D | d | E | е | e ₁ | L | L ₁ ⁽¹⁾ |
|------|------------|--------------|----------------|--------------|------------|------------|------------|------|----------------|--------------|-------------------------------|
| mm | 5.2 5.0 | 0.48 0.40 | 0.66 0.56 | 0.45 0.40 | 4.8 4.4 | 1.7 1.4 | 4.2 3.6 | 2.54 | 1.27 | 14.5 12.7 | 2.5 |

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

| OUTLINE | | REFERENCES | | | REFERENCES | | EUROPEAN | ISSUE DATE |
|---------|-----|------------|-------|--|------------|------------|----------|------------|
| VERSION | IEC | JEDEC | EIAJ | | PROJECTION | ISSUE DATE | | |
| SOT54 | | TO-92 | SC-43 | | | 97-02-28 | | |

PNP general purpose transistor

2N4126

DEFINITIONS

| Data sheet status | | | | |
|--|---|--|--|--|
| Objective specification | This data sheet contains target or goal specifications for product development. | | | |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. | | | |
| Product specification | This data sheet contains final product specifications. | | | |
| Limiting values | | | | |
| Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or | | | | |

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

LIFE SUPPORT APPLICATIONS

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PNP general purpose transistor

2N4126

NOTES

PNP general purpose transistor

2N4126

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